NSS30070MR6T1G

30 V, 0.7 A, Low $V_{CE(sat)}$ PNP Transistor

ON Semiconductor's e^2PowerEdge family of low $V_{CE(sat)}$ transistors are miniature surface mount devices featuring ultra low saturation voltage ($V_{CE(sat)}$) and high current gain capability. These are designed for use in low voltage, high speed switching applications where affordable efficient energy control is important.

Typical application are DC−DC converters and power management in portable and battery powered products such as cellular and cordless phones, PDAs, computers, printers, digital cameras and MP3 players. Other applications are low voltage motor controls in mass storage products such as disc drives and tape drives. In the automotive industry they can be used in air bag deployment and in the instrument cluster. The high current gain allows e^2PowerEdge devices to be driven directly from PMU's control outputs, and the Linear Gain (Beta) makes them ideal components in analog amplifiers.

- This is a Pb−Free Device

MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Collector−Emitter Voltage	V_{CEO}	30	V
Collector−Base Voltage	V_{CBO}	40	V
Emitter−Base Voltage	V_{EBO}	5.0	V
Collector Current	I_C	700	mA
Base Current	I_B	350	mA
Total Power Dissipation @ T_C = 25°C Total Power Dissipation @ T_C = 85°C Thermal Resistance − Junction−to−Ambient (Note 1)	P_D P_D $R_{\theta JA}$	342 178 366	mW mW °C/W
Total Power Dissipation @ T_C = 25°C Total Power Dissipation @ T_C = 85°C Thermal Resistance − Junction−to−Ambient (Note 2)	P_D P_D $R_{\theta JA}$	665 346 188	mW mW °C/W
Operating and Storage Temperature Range	T_J, T_{stg}	−55 to +150	°C

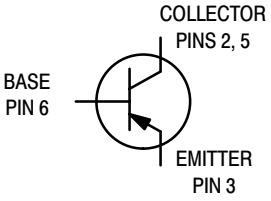
Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

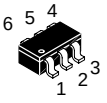
1. Minimum FR−4 or G−10 PCB, Operating to Steady State.
2. Mounted onto a 2″ square FR−4 Board (1″ sq. 2 oz Cu 0.06″ thick single sided), Operating to Steady State.

ON Semiconductor®

http://onsemi.com

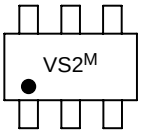
30 VOLTS
0.7 AMPS
PNP LOW $V_{CE(sat)}$ TRANSISTOR
EQUIVALENT $R_{DS(on)}$ 320 mΩ





SC−74
CASE 318F
STYLE 2

DEVICE MARKING



VS2 = Specific Device Code
M = Date Code

ORDERING INFORMATION

Device	Package	Shipping†
NSS30070MR6T1G	SC−74 (Pb−Free)	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector−Base Breakdown Voltage	(I_C = 100 μA)	$V_{(BR)CBO}$	40	−	−	V
Collector−Emitter Breakdown Voltage	(I_C = 10 mA)	$V_{(BR)CEO}$	30	−	−	V
Emitter−Base Breakdown Voltage	(I_E = 100 μA)	$V_{(BR)EBO}$	5.0	−	−	V
Collector Cutoff Current	(V_{CB} = 25 V, I_E = 0 A) (V_{CB} = 25 V, I_E = 0 A, T_A = 125°C)	I_{CBO}	− −	− −	1.0 10	μA
Emitter Cutoff Current	(V_{EB} = 5.0 V, I_C = 0 A)	I_{EBO}	−	−	10	μA
ON CHARACTERISTICS						
DC Current Gain	(V_{CE} = 3.0 V, I_C = 100 mA)	h_{FE}	150	−	−	V
Collector−Emitter Saturation Voltage	(I_C = 500 mA, I_B = 50 mA)	$V_{CE(sat)}$	−	−	0.25	V
Collector−Emitter Saturation Voltage	(I_C = 700 mA, I_B = 70 mA)	$V_{CE(sat)}$	−	−	0.4	V
Base−Emitter Saturation Voltage	(I_C = 700 mA, I_B = 70 mA)	$V_{BE(sat)}$	−	−	1.1	V
Collector−Emitter Saturation Voltage	(I_C = 700 mA, V_{CE} = 1.0 V)	$V_{BE(on)}$	−	−	1.0	V

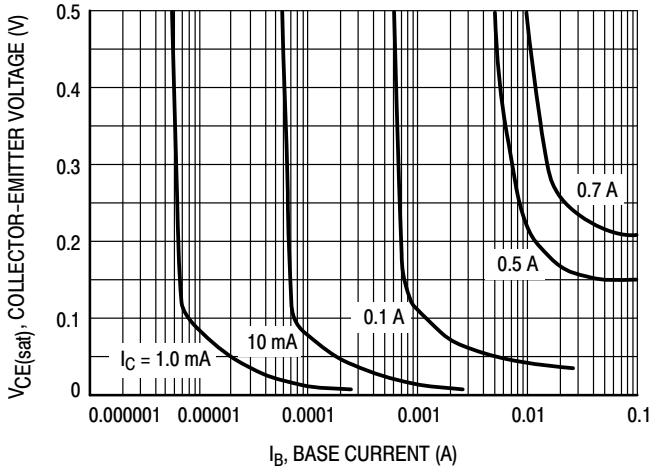


Figure 1. Collector Saturation Region

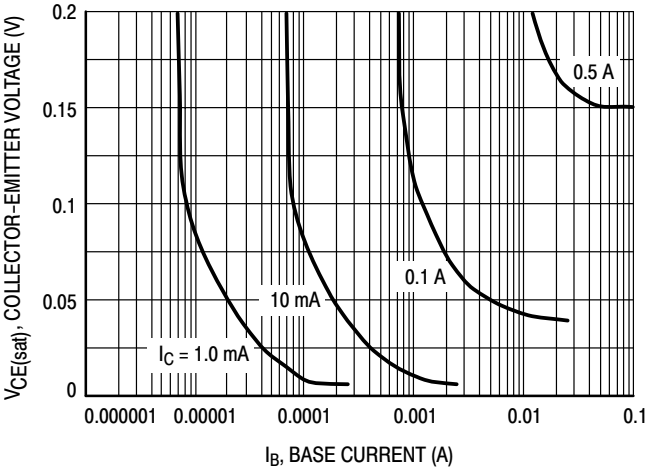


Figure 2. Collector Saturation Region

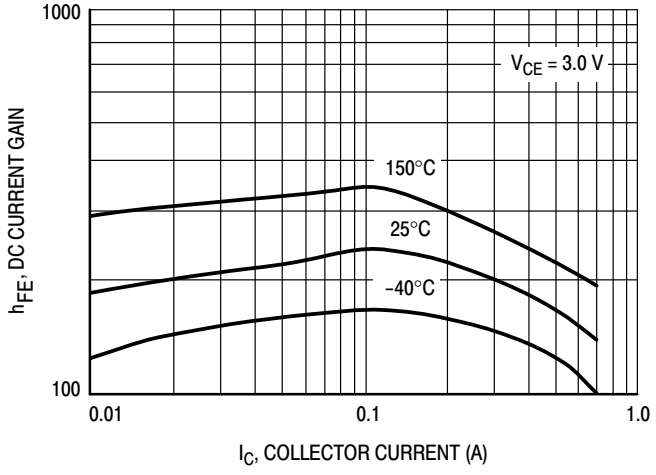


Figure 3. DC Current Gain

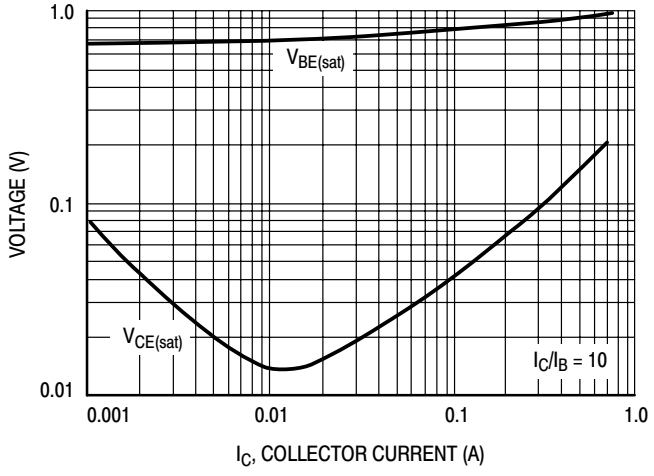


Figure 4. “ON” Voltages

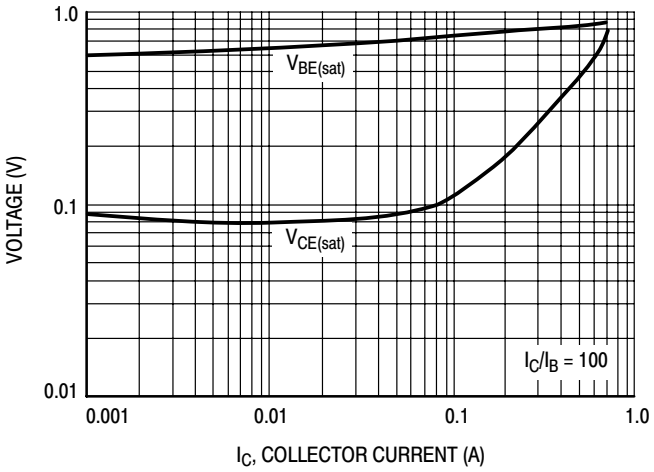


Figure 5. "ON" Voltages

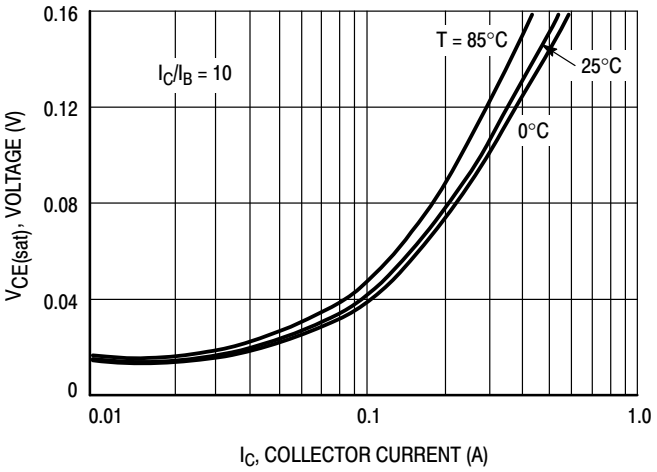


Figure 6. Collector−Emitter Saturation Voltage

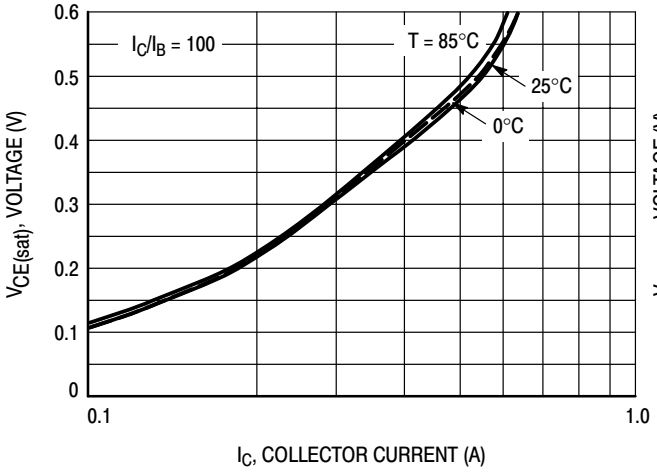


Figure 7. Collector−Emitter Saturation Voltage

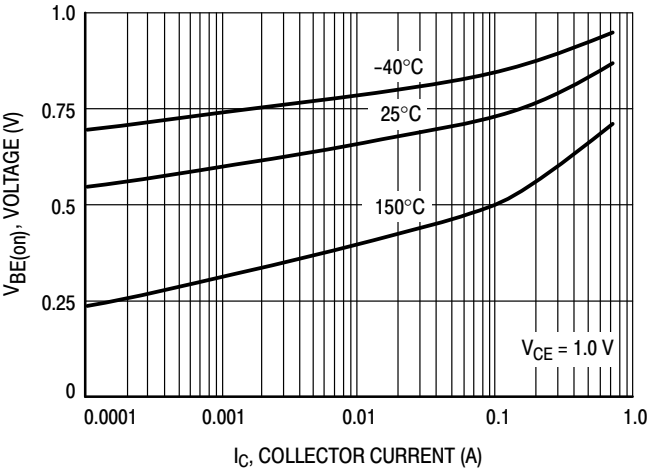


Figure 8. $V_{BE(on)}$ Voltage

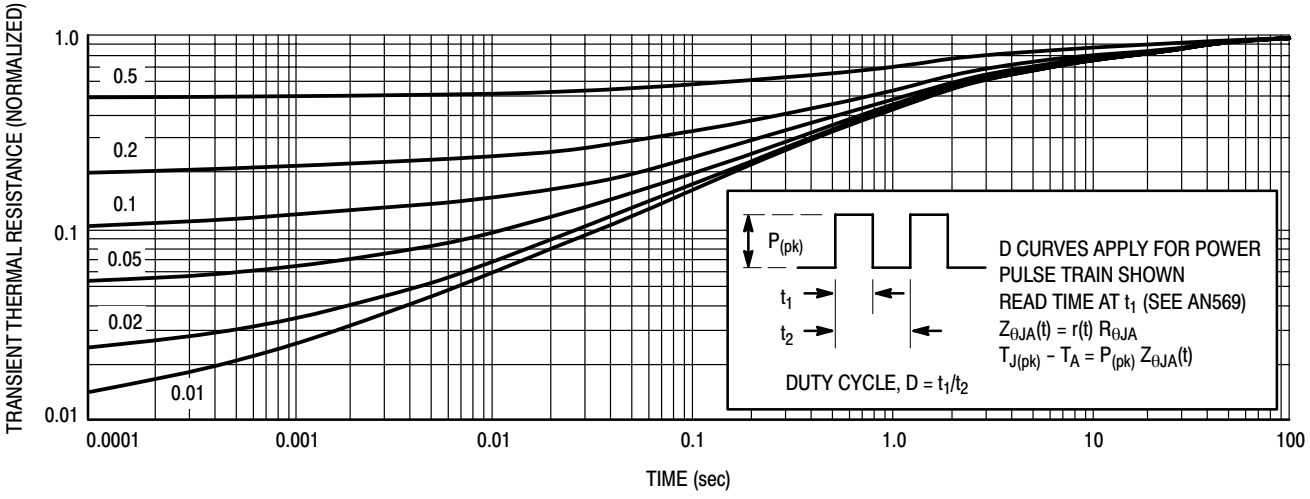
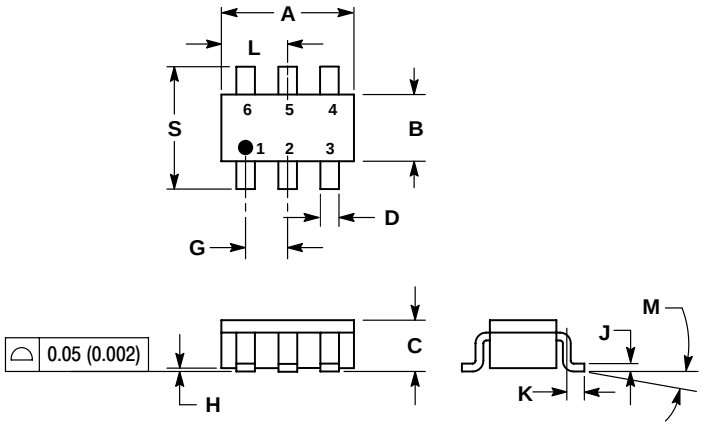


Figure 9. Thermal Response Curve

NSS30070MR6T1G

PACKAGE DIMENSIONS

SC−74
CASE 318F−05
ISSUE K

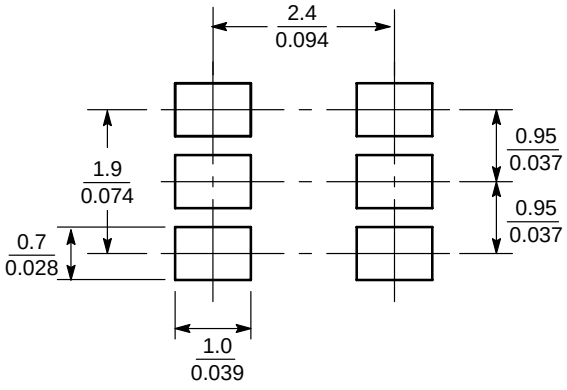


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. 318F−01, −02, −03 OBSOLETE. NEW STANDARD 318F−04.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.1142	0.1220	2.90	3.10
B	0.0512	0.0669	1.30	1.70
C	0.0354	0.0433	0.90	1.10
D	0.0098	0.0197	0.25	0.50
G	0.0335	0.0413	0.85	1.05
H	0.0005	0.0040	0.013	0.100
J	0.0040	0.0102	0.10	0.26
K	0.0079	0.0236	0.20	0.60
L	0.0493	0.0649	1.25	1.65
M	0 °	10 °	0 °	10 °
S	0.0985	0.1181	2.50	3.00

STYLE 2:
PIN 1. NO CONNECTION
2. COLLECTOR
3. EMITTER
4. NO CONNECTION
5. COLLECTOR
6. BASE

SOLDERING FOOTPRINT*



*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 61312, Phoenix, Arizona 85082−1312 USA
Phone: 480−829−7710 or 800−344−3860 Toll Free USA/Canada
Fax: 480−829−7709 or 800−344−3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800−282−9855 Toll Free USA/Canada

Japan: ON Semiconductor, Japan Customer Focus Center
2−9−1 Kamimeguro, Meguro−ku, Tokyo, Japan 153−0051
Phone: 81−3−5773−3850

ON Semiconductor Website: http://onsemi.com

Order Literature: http://www.onsemi.com/litorder

For additional information, please contact your local Sales Representative.

NSS30070MR6/D

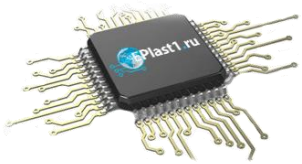
Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits,General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

Телефон: 8 (812) 309 58 32 (многоканальный)
Факс: 8 (812) 320-02-42
Электронная почта: org@eplast1.ru
Адрес: 198099, г. Санкт-Петербург, ул. Калинина, дом 2, корпус 4, литера А.